What is claimed is:

1. An article comprising:

a first sheet comprising a first sheet bonding surface;

a second sheet comprising a second sheet bonding surface;

a modification layer comprising a modification layer bonding surface, the modification layer comprising organosilicon; and

the modification layer bonding surface being in contact with the first sheet bonding surface, and the second sheet bonding surface being coupled with the first sheet bonding surface with the modification layer therebetween, wherein the first sheet bonding surface is bonded with the modification layer bonding surface with a bond energy of less than 600 mJ/m^2 after holding the article at 600° C for 10 minutes in a nitrogen atmosphere;

wherein the modification layer is a polymerized amorphous organosilicon and has a thickness in the range of 5 nm to 10 microns.

2. The article of claim 1, the first sheet bonding surface being bonded with the modification layer bonding surface with a bond energy of less than 600 mJ/m^2 after holding the article at 700° C for 10 minutes in a nitrogen atmosphere.

3. The article of claim 1 or claim 2, the modification layer comprising an atomic percent ratio of oxygen to silicon of less than 0.9, wherein the atomic percent of silicon and oxygen is measured from the modification layer prior to surface modification and being in contact with the first sheet bonding surface.

4. The article of any one of claims 1-3, the modification layer bonding surface comprising an atomic percent ratio of oxygen to silicon in the range of 1 to 3 and an atomic percent ratio of nitrogen to silicon in the range of 0.5 to 1.5, wherein the atomic percent of silicon, oxygen and nitrogen is measured from the modification

layer bonding surface after the modification layer bonding surface is exposed to nitrogen containing reactant to increase the surface energy of the modification layer bonding surface to a range of 55 to 75 mJ/m^2.

5. The article of any one of claims 1-4, the modification layer bonding surface comprising an atomic percent ratio of oxygen to silicon in the range of 1 to 3 and an atomic percent ratio of nitrogen to silicon in the range of 2.5 to 6.5, wherein the atomic percent of silicon, oxygen and nitrogen is measured from the modification layer bonding surface after the article is held at 700° C for 10 minutes in nitrogen containing reactant and then the first sheet is separated from the second sheet after the article is cooled to room temperature.

6. The article of any one of claims 1-5, the change in percent of blister area is less than 1 percent after the article is subjected to a temperature cycle by heating in a chamber cycled from room temperature to 700° C at a rate of 600° C per minute and held at 700° C for 10 minutes before allowing the article to cool to room temperature.

7. The article of any one of claims 1-6, wherein the first sheet may be separated from the second sheet without breaking the first sheet into two or more pieces after the article is subjected to a temperature cycle by heating in a chamber cycled from room temperature to 700° C at a rate of 600° C per minute and held at 700° C for 10 minutes before allowing the article to cool to room temperature.

8. The article of any one of claims 1-7, the first sheet being glass comprising a thickness of 300 microns or less, and the second sheet being glass comprising a thickness of 300 microns or greater.

9. A method of making an article comprising:

forming a modification layer on a bonding surface of a second sheet by depositing an organosilane monomer on the bonding surface of the second sheet, the modification layer comprising organosilicon and the modification layer comprising a modification layer bonding surface;

increasing the surface energy of the modification layer bonding surface; and

bonding the first sheet to the second sheet with the modification layer therebetween, wherein the bonding surface of the first sheet contacts the bonding surface of the modification layer;

wherein the modification layer is a polymerized amorphous organosilicon and has a thickness in the range of 5 nm to 10 microns.

10. The method of claim 9, the surface energy of the modification layer bonding surface being increased by exposure to nitrogen, oxygen, hydrogen, carbon dioxide gas or a combination thereof.

11. The method of claim 9 or claim 10, the modification layer is formed by deposition of a compound selected from the group consisting of phenylsilicon, methylphenylsilicon, diphenylsilicon, methlydiphenylsilicon and triphenylsilicon.

12. The method of any one of claims 9-11, the organosilane monomer comprising a formula $(R_1)_xSi(R_2)_y$, wherein R_1 is an aryl, alkyl, alkynyl and /or alkenyl and x is 1, 2 or 3, R_2 is hydrogen, halogen, an aryl, alkyl, alkynyl and /or alkenyl, or a combination thereof and y is 1, 2 or 3, wherein R_1 and R_2 are not oxygen.

13. The method of claim 12, R_1 or R_2 being an aryl, phenyl, tolyl, xylyl, naphthyl or a combination thereof.

14. The method of claim 12, R_2 being hydrogen, methyl or a combination thereof.

15. The method of claim 12, R_1 or R_2 being an aryl.

16. The method of claim 12, R_1 or R_2 being a di-aryl.

17. The method of claim 12, the organosilane monomer being selected from the group consisting of phenylsilane, methylphenylsilane, diphenylsilane, methlydiphenylsilane and triphenylsilane.

18. The method of claim 12, the organosilane monomer being free of an oxygen atom.

19. The method of any one of claims 9-18, the first sheet being glass comprising a thickness of 300 microns or less and the second sheet being glass comprising a thickness of 300 microns or greater.